

SILICON POWER TRANSISTOR 2SA1843

PNP SILICON EPITAXIAL POWER TRANSISTOR FOR HIGH-SPEED SWITCHING

The 2SA1843 is a power transistor developed for high-speed switching and features a high here at low VCE(sat). This transistor is ideal for use as a driver in DC/DC converters and actuators.

In addition, this transistor features a package that can be auto-mounted in radial taping specifications, thus contributing to mounting cost reduction.

FEATURES

- Auto-mounting possible in radial taping specifications
- Resin-molded insulation type package with power rating of 1.8 W in stand-alone conditions
- High hee and low VCE(sat):

 $V_{CE(sat)} \le -0.3 \text{ V}$ @ Ic = -3.0 A, IB = -0.15 A hFE ≥ 100 @ VcE = -2.0 V, Ic = -1.0 A

· Fast switching speed

ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		-100	٧
Collector to emitter voltage	VCEO		-60	V
Emitter to base voltage	VEBO		-7.0	V
Collector current (DC)	Ic(DC)		-5.0	Α
Collector current (pulse)	IC(pulse)	PW ≤ 300 μs, duty cycle ≤ 2%	-10	Α
Base current (DC)	I _{B(DC)}		-2.5	Α
Total power dissipation	Рт	Ta = 25°C	1.8	W
Junction temperature	Tj		150	°C
Storage temperature	Tstg		−55 to +150	°C

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ELECTRICAL CHARACTERISTICS (Ta = 25°C)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Collector cutoff current	Ісво	Vcb = -60 V, IE = 0			-10	μΑ
Collector cutoff current	ICER	$V_{CE} = -60$ V, $R_{EB} = 50$ Ω $Ta = 125$ °C			-1.0	mA
Collector cutoff current	ICEX1	Vce = -60 V, VBE(off) = 1.5 V	VCE = -60 V, VBE(off) = 1.5 V		-10	μΑ
Collector cutoff current	ICEX2	Vce = -60 V, Vbe(off) = 1.5 V Ta = 125°C			-1.0	mA
Emitter cutoff current	ІЕВО	V _{EB} = -5.0 V, I _C = 0			-10	μΑ
DC current gain	hFE1*	Vce = -2.0 V, Ic = -0.5 A	100			
DC current gain	h _{FE2} *	Vce = −2.0 V, lc = −1.0 A	100		400	-
DC current gain	h _{FE3} *	Vce = -2.0 V, Ic = -3.0 A	60			-
Collector saturation voltage	VCE(sat)1*	Ic = -3.0 A, Iв = -0.15 A			-0.3	V
Collector saturation voltage	VCE(sat)2*	Ic = -4.0 A, IB = -0.2 A			-0.5	V
Base saturation voltage	V _{BE(sat)1} *	Ic = -3.0 A, Iв = -0.15 A			-1.2	V
Base saturation voltage	V _{BE(sat)2} *	Ic = -4.0 A, I _B = -0.2 A			-1.5	V
Gain bandwidth product	f⊤	$V_{CE} = -10 \text{ V}, \text{ Ic} = -0.5 \text{ A}$		80		MHz
Collector capacitance	Соь	V _{CB} = -10 V, I _E = 0, f = 1 MHz		130		pF
Turn-on time	ton	Ic = -3.0 A		0.15		μs
Storage time	tstg	$I_{B1} = -I_{B2} = -0.15 \text{ A}$ $R_L = 17 \Omega, \text{ Vcc} = -50 \text{ V}$		1.0		μs
Fall time	tf	11L - 17 52, VCC = -50 V		0.1		μs

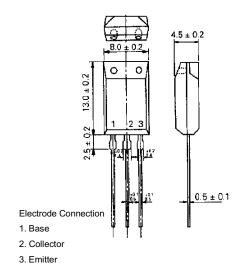
^{*} Pulse test PW \leq 350 μ s, duty cycle \leq 2%

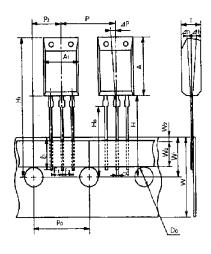
hfe CLASSIFICATION

Marking	M	L	K	
hfe	100 to 200	150 to 300	200 to 400	

PACKAGE DRAWING (UNIT: mm)

TAPING SPECIFICATION

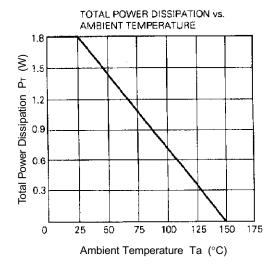


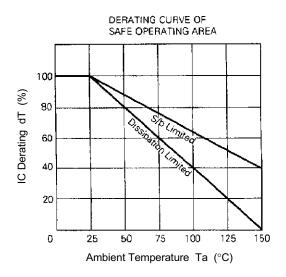


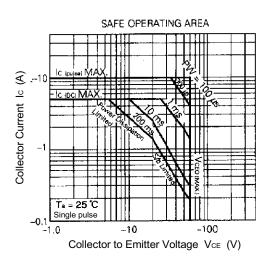
Αı	8.0 ± 0.2
Α	13.0 ± 0.2
Do	$\phi 4.0 \pm 0.2$
ď	0.5 ± 0.1
Fi	2.5+0.4
F ₂	2.5+0.4
Н	20.0 MAX.
Ho	16.0 ± 0.5
Hi	32.2 MAX.
⊿h	0 ± 1.0
l:	2.5 MIN.
P	12.7 ± 1.0
Po	12.7 ± 0.3
P ₂	6.35 ± 0.5
⊿P	0 ± 1.3
Т	4.5 ± 0.2
W	18.0 ^{±1.0} _{-0.5}
Wo	5.0 MIN.
W_1	9.0 ± 0.5
M ⁵	0.7 MIN.

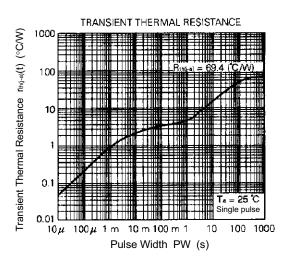


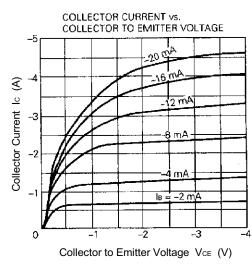
TYPICAL CHARACTERISTICS (Ta = 25°C)

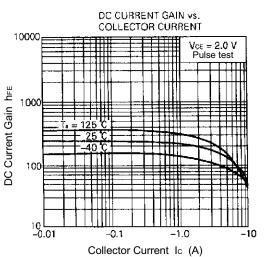




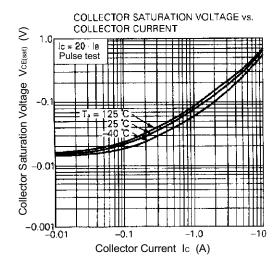


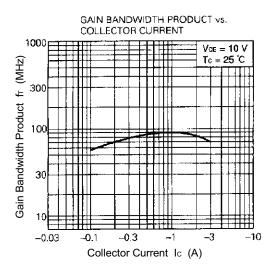


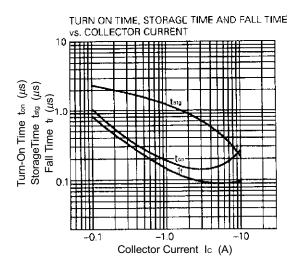


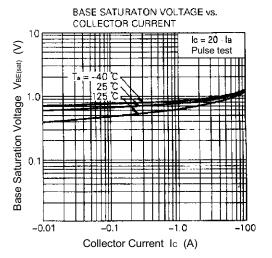


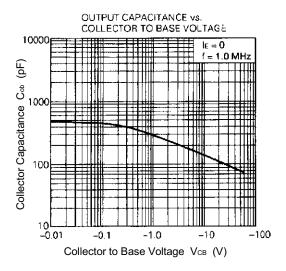
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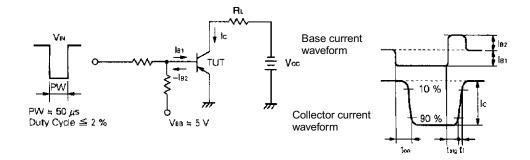








SWITCHING TIME (ton, tstg, tf) TEST CIRCUIT



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